

Description

The HSS6014 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

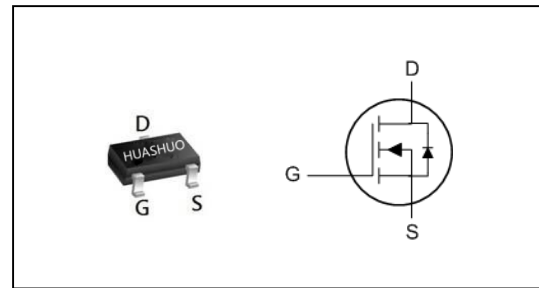
The HSS6014 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	60	V
$R_{DS(ON),max}$	40	m Ω
I_D	6	A

SOT-23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.5	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.5	A
I_{DM}	Pulsed Drain Current ²	18	A
I_{AS}	Avalanche Current	21	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	2.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	95	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.044	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =4A	---	33	40	mΩ
		V _{GS} =4.5V, I _D =2A	---	40	50	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.8	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	---	25.3	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =48V, V _{GS} =10V, I _D =5A	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	2.5	---	
Q _{gd}	Gate-Drain Charge		---	4.1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω I _D =5A	---	2.8	---	ns
T _r	Rise Time		---	34	---	
T _{d(off)}	Turn-Off Delay Time		---	21.2	---	
T _f	Fall Time		---	5.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1027	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	46	---	

Diode Characteristics

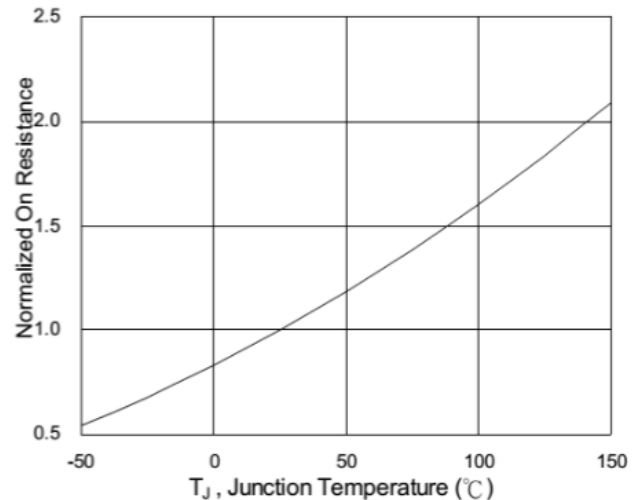
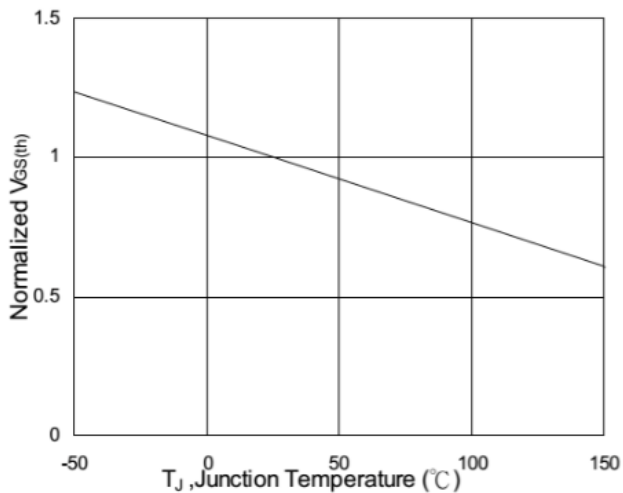
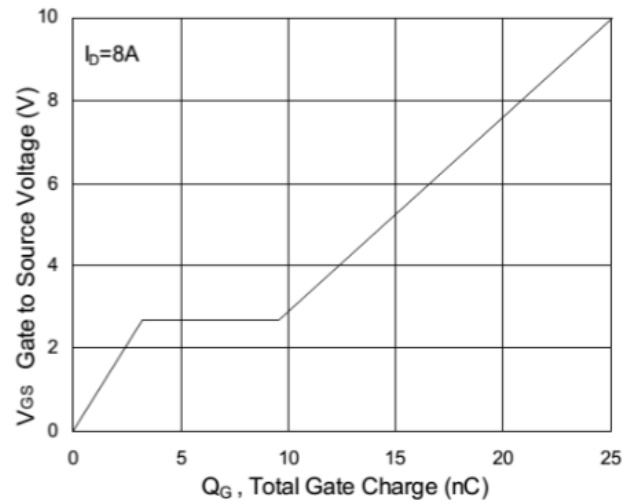
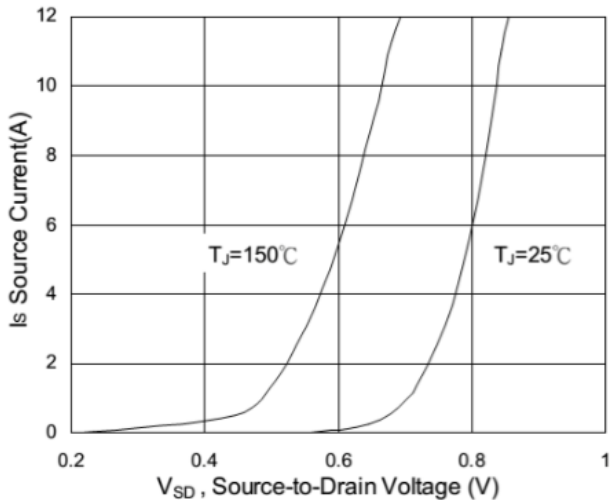
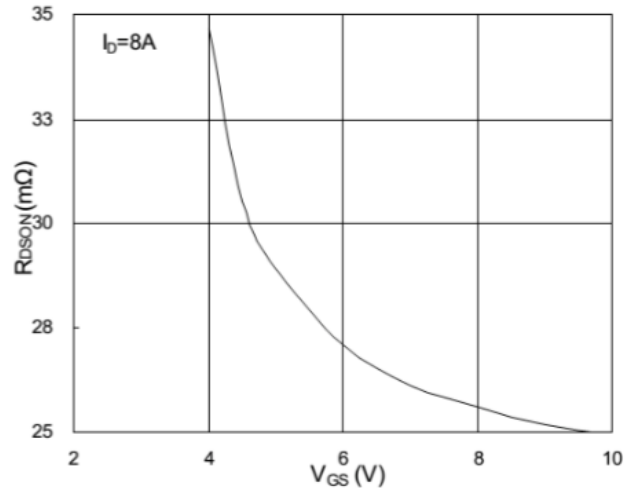
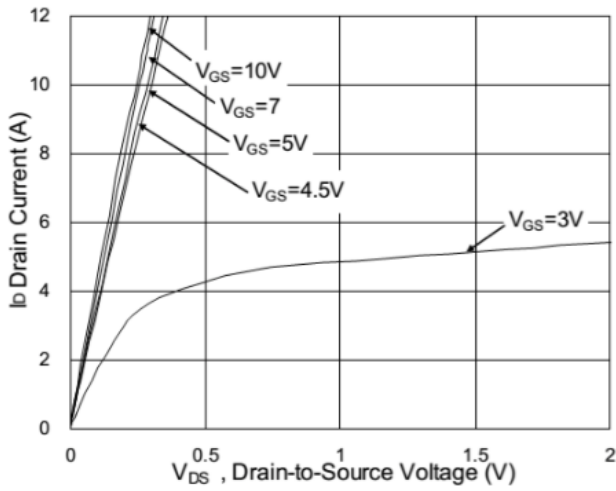
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	4.5	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	6	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =15A, dI/dt=100A/μs, T _J =25°C	---	12.2	---	nS
Q _{rr}	Reverse Recovery Charge		---	7.3	---	nC

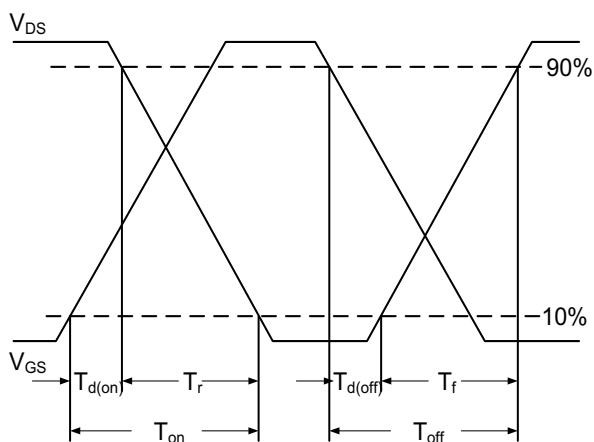
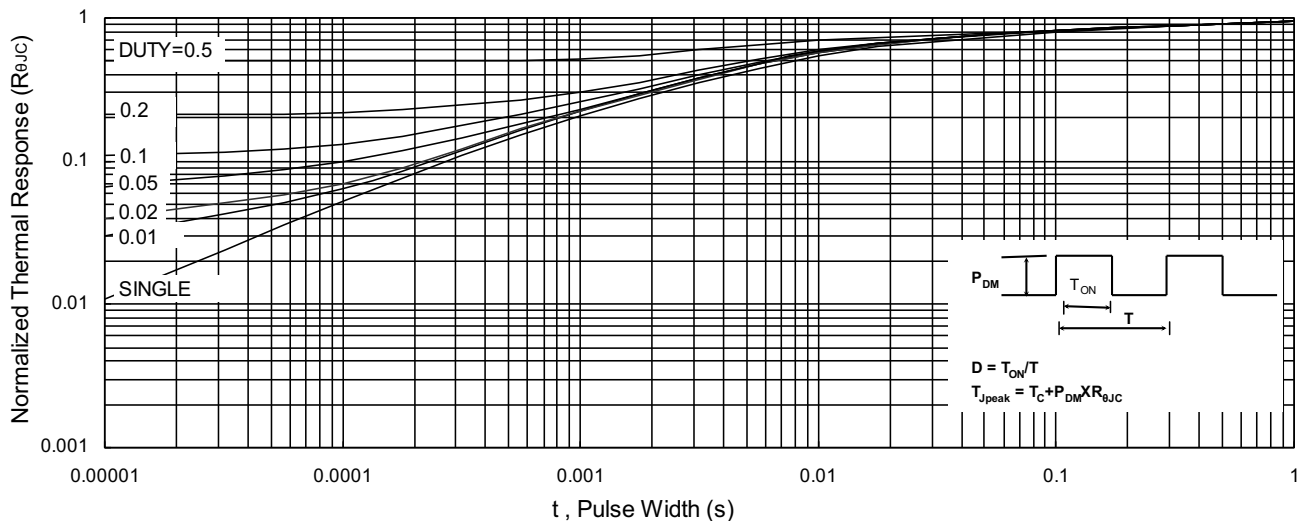
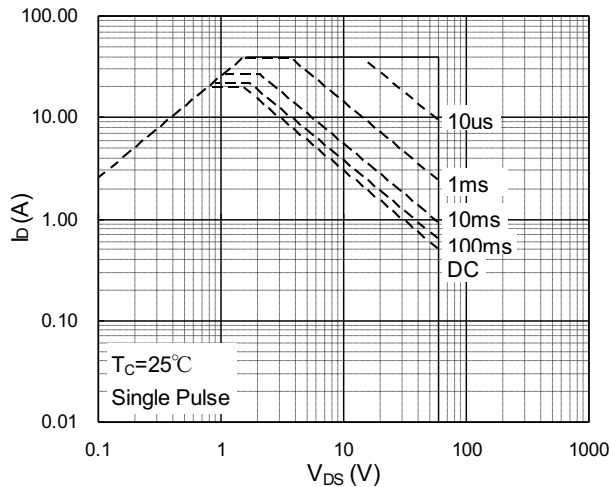
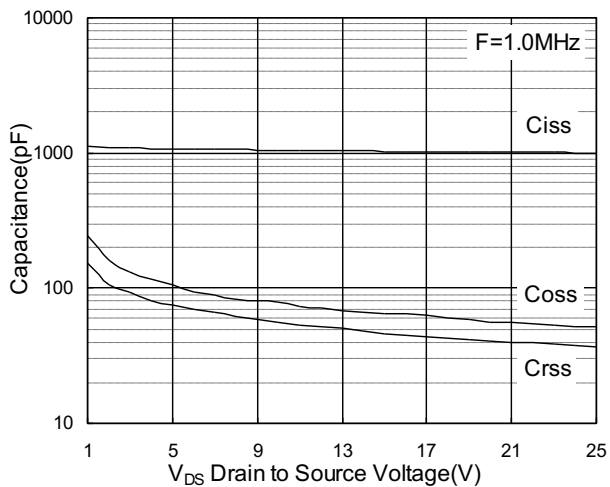
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

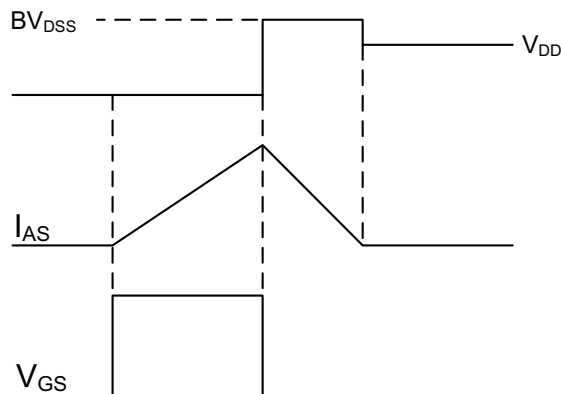


Typical Characteristics





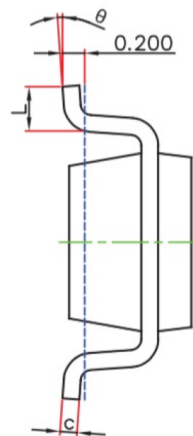
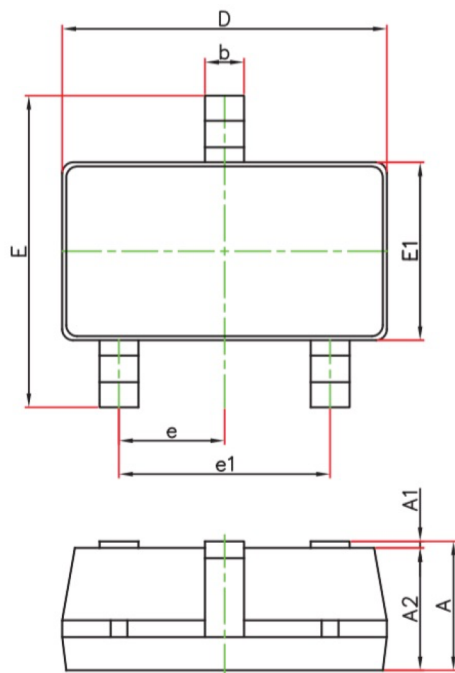
$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$





Ordering Information

Part Number	Package code	Packaging
HSS6014	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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